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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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Substitute for form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	Based on SN 10/035,441
				Filing Date	Filed: January 4, 2002
				First Named Inventor	Naoaki YAMAGUCHI et al.
				Group Art Unit	1765
				Examiner Name	Anita Karen Alanko
Sheet	1	of	3	Attorney Docket Number	0756-7191

U.S. PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
CL		5,808,318		Masumo et al.	09/15/1998	
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		Office ³	Number ⁴	Kind Code ² (if known)				
CL		JP	05-243576			09/21/1993		Abst.
CL		JP	08-051078			02/20/1996		Abst.
CL		JP	06-204132			07/22/1994		Abst.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials [*]	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ³
CL		F. Ueno "Observation of fast microscopic phase change phenomena of chalcogenide thin films," Japanese Journal of Applied Physics, Supplement, Vol. 26, Supplement 26-4, pp. 55-60, 1987.	
CL		N. Kondo et al., "Film thickness measurement of ultrathin film using light of UV wavelength," Proceedings of the SPIE, Vol. 1673, pp. 392-402, 1992.	

Examiner Signature	<i>Calvin U</i>	Date Considered	6.20.05
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CL		A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," USSR, pp. 635-640, Phys. Stat. Sol. (A) Vol. 95, 1986.	
CL		T. Hempel et al., "Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films," Solid State Communications, Vol. 85, No. 11, pp. 921-924, 1993.	
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Examiner Signature	<i>calomlu</i>	Date Considered	6.30.05
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CL		G. Liu, S.J. Fonash, "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low Temperature Processing," Appl. Phys. Lett 62 (20), May 17, 1993, 1993 American Institute of Physics, pp. 2554-2556.	
CL		G. Liu and S.J. Fonash, "Selective Area Crystallization of Amorphous Silicon Films by Low-Temperature Rapid Thermal Annealing," Appl. Phys. Lett 55 (7), August 14, 1989, American Institute of Physics, pp. 660-662	
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